

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

XPJR6604PB

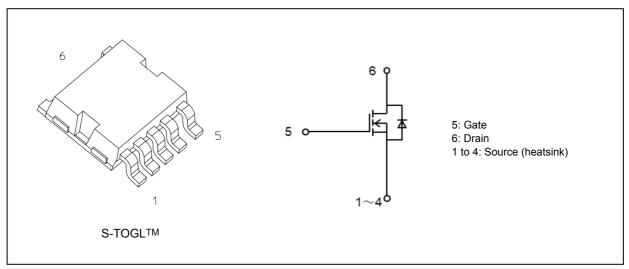
1. Applications

- · Automotive
- · Switching Voltage Regulators
- · Motor Drivers
- · DC-DC Converters

2. Features

- (1) AEC-Q101 qualified
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 0.53 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (3) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$
- (4) Enhancement mode: V_{th} = 2.0 to 3.0 V (V_{DS} = 10 V, I_D = 1.0 mA)

3. Packaging and Internal Circuit Pin Assignment (Note)



Note: S-TOGLTM is a trademark of Toshiba Electronic Devices & Storage Corporation.

Rev.2.0



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	40	V
Gate-source voltage		V _{GSS}	±20	
Drain current (DC)	(Note 1)	I _D	200	Α
Drain current (pulsed)	(Note 1)	I _{DP}	600	
Power dissipation	(T _c = 25 °C)	P _D	375	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	494	mJ
Single-pulse avalanche current		I _{AS}	100	Α
Channel temperature	(Note 3)	T _{ch}	175	ç
Storage temperature	(Note 3)	T _{stg}	-55 to 175	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

	Characteristics	Symbol	Max	Unit
Channel-to-case thermal impedance	(T _c = 25 °C)	Z _{th(ch-c)}	0.4	°C/W

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: V_{DD} = 32 V, T_{ch} = 25 °C (initial), L = 38 μ H, R_{G} = 25 Ω , I_{AS} = 100 A

Note 3: The definitions of the absolute maximum channel and storage temperatures are based on AEC-Q101.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V			10	
Drain-source breakdown voltage	V _{(BR)DSS}	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	40			٧
	V _{(BR)DSX}	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	20	_	_	
Gate threshold voltage (Note 4)	V_{th}	V _{DS} = 10 V, I _D = 1.0 mA	2.0	_	3.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 6 V, I _D = 100 A	_	0.75	1.16	mΩ
		V _{GS} = 10 V, I _D = 100 A	_	0.53	0.66	

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 300 kHz	_	8750	11380	pF
Reverse transfer capacitance	C _{rss}		_	780	1100	
Output capacitance	C _{oss}		_	5420	_	
Gate resistance	r _g		_	2.9	5.8	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	42	_	ns
Switching time (turn-on time)	t _{on}		_	73		
Switching time (fall time)	t _f		_	54	_	
Switching time (turn-off time)	t _{off}		_	152	_	

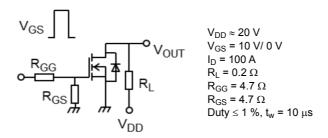


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 200 \text{ A}$		128	_	nC
Gate-source charge 1	Q _{gs1}			43	_	
Gate-drain charge	Q_{gd}			29		

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 5)	I _{DR}	_	_	_	200	Α
Reverse drain current (pulsed)	(Note 5)	I _{DRP}	_	_	_	600	
Diode forward voltage		V_{DSF}	I _{DR} = 200 A, V _{GS} = 0 V	_	_	-1.2	V
Reverse recovery time		t _{rr}	I _{DR} = 200 A, V _{GS} = 0 V	_	84	_	ns
Reverse recovery charge	·	Q_{rr}	-dI _{DR} /dt = 100 A/μs	_	151		nC

Note 5: Ensure that the channel temperature does not exceed 175 °C.



7. Marking

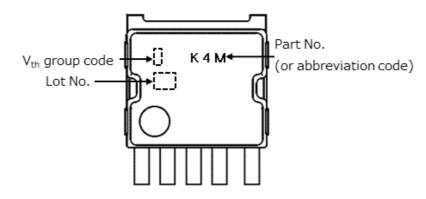


Fig. 7.1 Marking

Note 4: If requested, V_{th} grouping is possible for each reel. (V_{th} width is 0.4 V) However, we do not accept specifications in specific groups.

If there is no request, the group-free reel will be applied. (V_{th} width is 1.0 V, no V_{th} group code is printed on marking)



8. Characteristics Curves (Note)

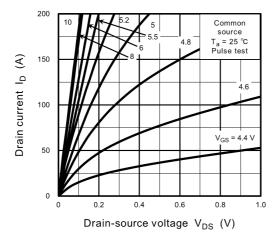


Fig. 8.1 I_D - V_{DS}

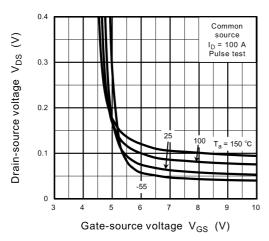


Fig. 8.3 V_{DS} - V_{GS}

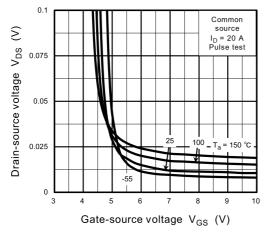


Fig. 8.5 V_{DS} - V_{GS}

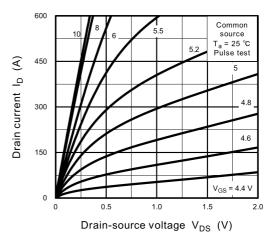


Fig. 8.2 I_D - V_{DS}

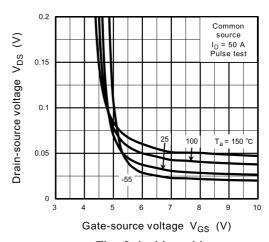


Fig. 8.4 V_{DS} - V_{GS}

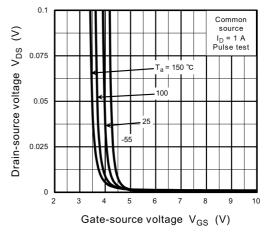


Fig. 8.6 V_{DS} - V_{GS}



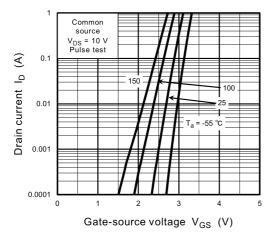


Fig. 8.7 ID - VGS

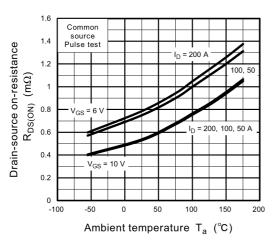


Fig. 8.9 R_{DS(ON)} - T_a

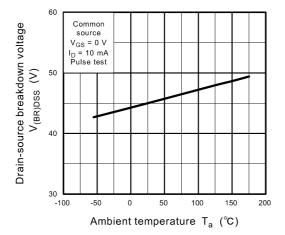


Fig. 8.11 V_{(BR)DSS} - T_a

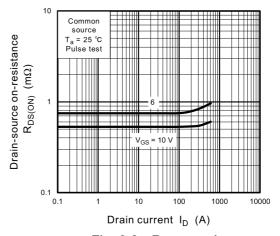


Fig. 8.8 R_{DS(ON)} - I_D

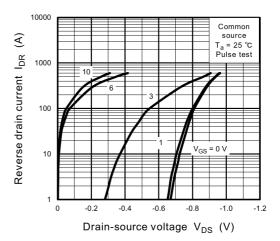


Fig. 8.10 I_{DR} - V_{DS}

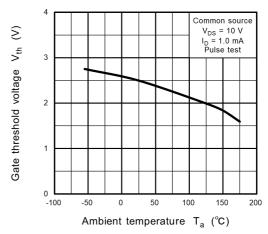


Fig. 8.12 V_{th} - T_a



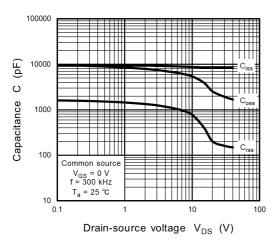


Fig. 8.13 Capacitance - V_{DS}

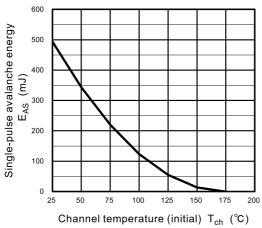


Fig. 8.15 E_{AS} - T_{ch}(Guaranteed Maximum)

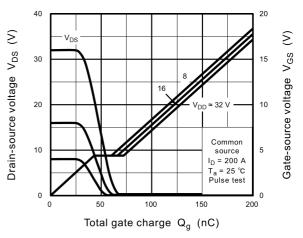


Fig. 8.14 Dynamic Input/Output Characteristics

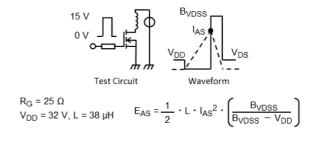


Fig. 8.16 Test Circuit/Waveform



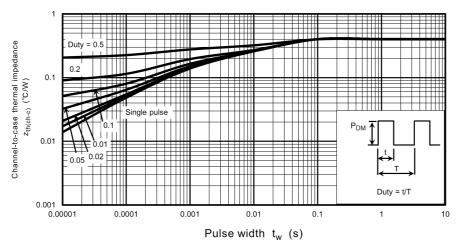
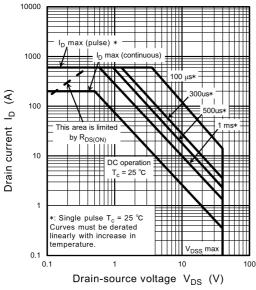


Fig. 8.17 $z_{th(ch-c)} - t_w$ (Guaranteed Maximum)





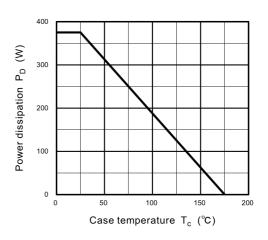


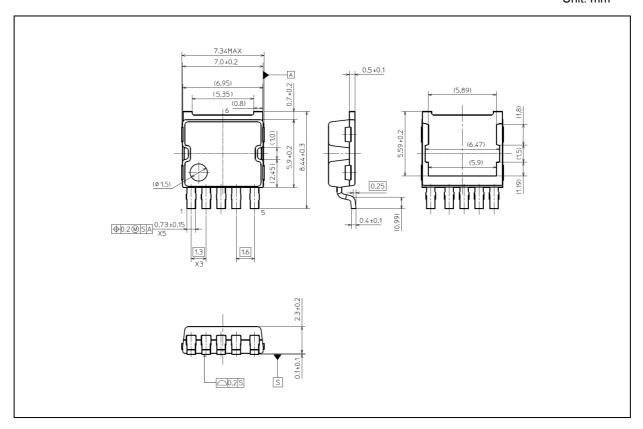
Fig. 8.19 P_D - T_c (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.395 g (typ.)

Package Name(s)
TOSHIBA: 2-7P1A
Nickname: S-TOGL™



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